

Si Photo-diode Chip—TK0120PDN

1. Scope

- The specification applies to PIN silicon photo-diode chips.
- Type : TK0120PDN.

2. Structure

- PIN planar type.
- Electrode topside (anode) : Aluminum.
- Electrode backside (cathode) : Gold.

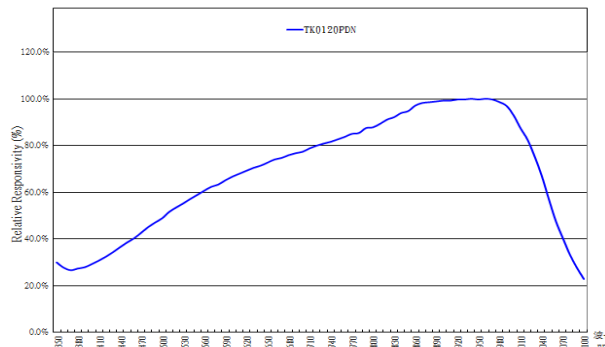
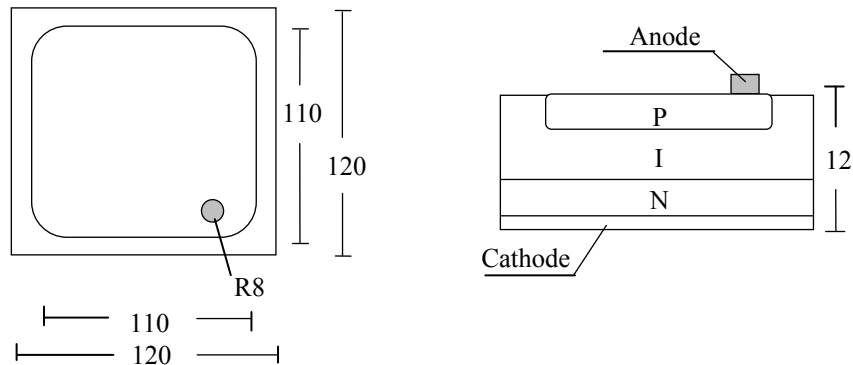
3. Size

- Chip size : 120mil × 120mil ± 1.5mil (3.050mm × 3.050mm ± 0.038mm)
- Thickness : 12mil ± 1mil (0.300mm ± 0.025mm)
- Active area : 110mil × 110mil ± 0.5mil (2.794mm × 2.794mm ± 0.013mm)
- Pad size : diameter 8mil ± 0.4mil (0.203mm ± 0.01mm)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V _F	I _F =10mA, H=0	0.5		1.3	V
Reverse Breakdown Voltage	V _{BR}	I _R =100μA, H=0	100			V
Reverse Dark Current	I _D	V _R =5V, H=0			10	nA
Light Current	I _L	V _R =5V, H as 1mw/cm ² @940nm		170		μA
Peak Sensing Wavelength	λ _p			940		nm
Total Capacitance	C _t	Ee=0mW/cm ² , V _R =3V, f=1 MHz		7.3		pF



Unit : mil

fig. 1

2016.Mar



☐ TYNTEK Head Office
☐ TYNTEK Chunan Branch
[http : //www.tyntek.com.tw](http://www.tyntek.com.tw)

Tel : 886-3-5781616
Tel : 886-37-582997

E-mail : service@serv.tyntek.com.tw

Fax : 886-3-5780545
Fax : 886-37-582908